# 4V Drive Pch MOS FET **RSR020P03**

#### Structure

Silicon P-channel MOS FET

#### Features

- 1) Low On-resistance
- 2) Space saving-small surface mount package (TSMT3)
- 3) 4V drive

#### Applications

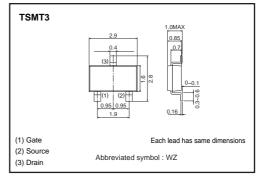
Switching

#### Packaging specifications

	Package	Taping	
Туре	Code	TL	
	Basic ordering unit (pieces)	3000	
RSR020P03	0		

#### •External dimensions (Unit : mm)

Inner circuit



# (3) (1) 0 (1) Gate (2) Source (2)\*1 ESD PROTECTION DIODE \*2 BODY DIODE

(3) Drain

#### Absolute maximum ratings (Ta=25°C)

Parameter Drain-source voltage		Symbol	Limits	Unit V V	
		V <sub>DSS</sub>	-30		
Gate-source voltage		Vgss	±20		
Desia sument	Continuous	ID	±2	А	
Drain current	Pulsed	I <sub>DP</sub> *1	±8	А	
Source current	Continuous	ls	-0.8	А	
(Body diode)	Pulsed	Ise *1	-8	А	
Total power dissipation		P <sub>D</sub> *2	1	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

\*1 Pw≤10µs, Duty cycle≤1%

\*2 Mounted on a ceramic board

#### Thermal resistance

Parameter	Symbol	Limits	Unit	
Channel to ambient	Rth(ch-a)*	125	°C/W	

\* Mounted on a ceramic board



# Transistors

### •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	±10	μA	Vgs=±20V, Vds=0V
Drain-source breakdown voltage	V(BR) DSS	-30	-	-	V	I <sub>D</sub> = –1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	-	-1	μΑ	$V_{DS}$ = -30V, $V_{GS}$ =0V
Gate threshold voltage	VGS (th)	-1.0	-	-2.5	V	$V_{DS} = -10V, I_{D} = -1mA$
Static drain-source on-state resistance		_	85	120	mΩ	$I_D = -2A$ , $V_{GS} = -10V$
	$R_{DS}(on)^*$	_	135	190	mΩ	$I_D = -1A$ , $V_{GS} = -4.5V$
		_	150	210	mΩ	$I_D = -1A$ , $V_{GS} = -4V$
Forward transfer admittance	Y <sub>fs</sub> *	1.4	-	_	S	$V_{DS} = -10V, I_{D} = -1A$
Input capacitance	Ciss	_	370	_	pF	V <sub>DS</sub> =-10V
Output capacitance	Coss	-	80	-	рF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	55	-	рF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	8	-	ns	V <sub>DD</sub> ≒−15V
Rise time	tr *	-	10	-	ns	$I_{D}=-1A$
Turn-off delay time	t <sub>d (off)</sub> *	-	35	_	ns	VGs= – 10V R∟=15Ω
Fall time	t <sub>f</sub> *	-	11	-	ns	Rg=10Ω
Total gate charge	Qg *	-	4.3	-	nC	V <sub>DD</sub> ≒−15V V <sub>GS</sub> =−5V
Gate-source charge	Q <sub>gs</sub> *	-	1.4	-	nC	I <sub>D</sub> =-2A
Gate-drain charge	Q <sub>gd</sub> *	-	1.5	-	nC	R∟=7.5Ω R <sub>G</sub> =10Ω

## •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd*	-	-	-1.2	V	I <sub>S</sub> = -0.8A, V <sub>GS</sub> =0V
*Pulsed						

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